TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

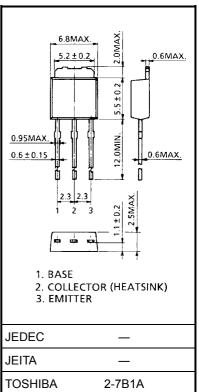
2SC2983

Power Amplifier Applications Driver Stage Amplifier Applications

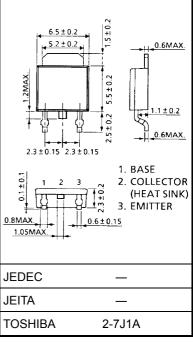
- High transition frequency: $f_T = 100 \text{ MHz}$ (typ.)
- Complementary to 2SA1225

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-base voltage		V _{CBO}	160	V	
Collector-emitter voltage		V _{CEO}	160	V	
Emitter-base voltage		V _{EBO}	5	V	
Collector current		Ι _C	1.5	А	
Base current		Ι _Β	0.3	А	
Collector power dissipation	Ta = 25°C	Pc	1.0	W	
	Tc = 25°C	гC	15		
Junction temperature		Тj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	



Weight: 0.36 g (typ.)



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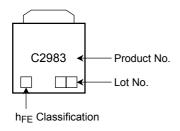
Unit: mm

Electrical Characteristics (Ta = 25°C)

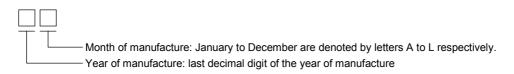
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 160 V, I _E = 0	_	—	1.0	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	1.0	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 A, I _B = 0	160	_	-	V
Emitter-base breakdown voltage	V (BR) EBO	I _E = 1 mA, I _C = 0	5	_	_	V
DC current gain	h _{FE} (Note)	V _{CE} = 5 V, I _C = 100 mA	70	_	240	
Collector emitter saturation voltage	V _{CE (sat)}	I _C = 500 mA, I _B = 50 mA	_	_	1.5	V
Base-emitter voltage	V _{BE}	V _{CE} = 5 V, I _C = 500 mA	_	_	1.0	V
Transition frequency	fT	V _{CE} = 10 V, I _C = 100 mA	_	100	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	25	_	pF

Note: hFE classification O: 70 to 140, Y: 120 to 240

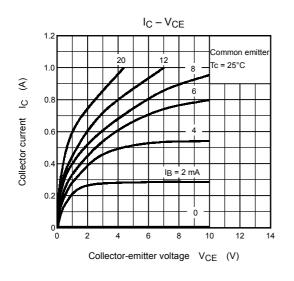
Marking

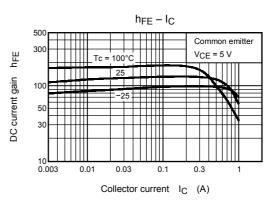


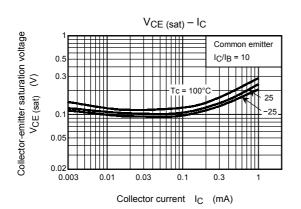
Explanation of Lot No.

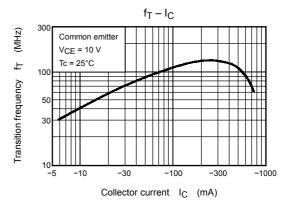


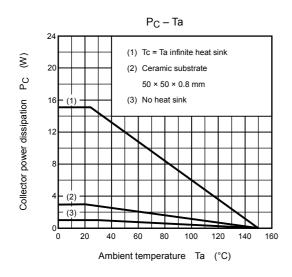
TOSHIBA

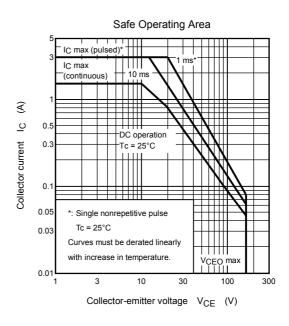












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